Amendments to the Claims:

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

1 - 13. (Canceled)

14. (Currently amended): A method of inspecting particles or defects comprising the steps of:

irradiating an object under inspection with light;

detecting reflected light or scattered light from the object under inspection;

detecting particles or defects based on a signal indicative of detected reflected light or scattered light;

processing the signal indicative of detected reflected light or scattered light to measure a size of each particle or defect;

processing data including the signal indicative of detected reflected light or scattered light, and a result of measuring the size of each particle or defect; and

displaying the result of data processing,

wherein ~~said~~ the step of processing data includes dividing the object under inspection into several regions, and processing data for each of the regions~~.~~,

wherein the step of displaying includes presenting a graphical indication of a size distribution of the particles or defects in each of the regions.

15. (Original): A method of inspecting particles or defects according to claim 14, wherein said step of displaying includes displaying particles or defects having a particular size in a manner discriminative from the remaining particles or defects for each of the regions.

16. (Original): A method of inspecting particles or defects according to claim 14, wherein said step of displaying includes displaying a distribution of frequencies for the particle or defect sizes in each of the regions.

17 - 20. (Canceled)

21. (Previously presented): A method as in claim 14 further comprising displaying a distribution of frequencies for particle or defect sizes measured.

22. (Previously presented): A method as in claim 14 further comprising displaying particles or defects having a particular size in a manner to discriminate particles or defects of that particular size from particles or defects of other sizes.

23. (New): A method as in claim 14, wherein the object is a semiconductor wafer on which a plurality of dies are formed, and the regions are divided according to a plurality of circuit pattern densities formed on the dies.

24. (New): A method as in claim 23 wherein for each die, each of the circuit pattern densities differs from one another, and each of regions respectively correspond to one of the circuit pattern densities, a minimum size of particles or defect in each of the regions being different from one another.